#### Practitioner's Docket No. MI22-2500

**PATENT** 

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: David L. Dickerson et al.

Application No.: 10/799,794

Filed: 03/11/04

Group No.: 2814 Examiner: A. Mai

For: Isolation Region Forming Methods

Commissioner for Patents Washington, D.C. 20231

## CERTIFICATION OF FACSIMILE TRANSMISSION

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(Certification of Facsimile Transmission-page 1 of 1)

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No
Filing Date March 11, 2004
Inventor
Assignee Micron Technology, Inc.
Group Art Unit
Examiner A.D. Mai
Attorney's Docket No MI22-2500
Title: Isolation Region Forming Methods

### SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - - See attached Form PTO-1449

The attached Form PTO-1449 is submitted in compliance with 37 C.F.R. §§ 1.56. Pursuant to Federal Register Vol. 69, No. 182, pg. 56542 (September 21, 2004), no copies of any cited U.S. patents or U.S. published applications are included herewith. Copies of all other cited art references, if any, are attached. No admission is made regarding whether the submitted reference is prior art.

Citation of this reference is respectfully requested.

Respectfully submitted,

Date: 3-23-05

D. Brent Kenady Reg. No. 40,045 (509) 624-4276

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